



DGD2103M

#### HALF-BRIDGE GATE DRIVER IN SO-8

#### Description

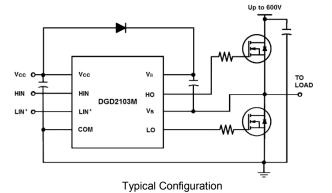
The DGD2103M is a high-voltage/high-speed gate driver capable of driving N-channel MOSFETs and IGBTs in a half-bridge configuration. High-voltage processing techniques enable the DGD2103M's high side to switch to 600V in a bootstrap operation.

The DGD2103M logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) to interface easily with controlling devices. The driver output features high-pulse current buffers designed for minimum driver cross conduction. DGD2103M has a fixed internal deadtime of 420ns (typical).

The DGD2103M is offered in the SO-8 package and operates over an extended -40°C to +125°C temperature range.

#### **Applications**

- DC-DC Converters
- DC-AC Inverters
- AC-DC Power Supplies
- Motor Controls
- Class D Power Amplifiers



#### Ordering Information (Note 4)

Product	Marking	Reel Size (inch)	Tape Width (mm)	Quantity per Reel
DGD2103MS8-13	DGD2103M	13	12	2500

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

#### **Marking Information**



) | | = Manufacturer's Marking DGD2103M = Product Type Marking Code YY = Year (ex: 19 = 2019) WW = Week (01 to 53)

#### October 2019 © Diodes Incorporated

# Features

- Floating High-Side Driver in Bootstrap Operation to 600V
- Drives Two N-Channel MOSFETs or IGBTs in a Half-Bridge Configuration
- Designed for Enhanced Performance in Noisy Motor Applications
- 290mA Source/600mA Sink Output Current Capability
- Outputs Tolerant to Negative Transients
- Internal Dead Time of 420ns to Protect MOSFETs
- Wide Low-Side Gate Driver Supply Voltage: 10V to 20V
- Logic Input (HIN and LIN\*) 3.3V Capability
- Schmitt Triggered Logic Inputs
- Undervoltage Lockout for V<sub>CC</sub> (Logic and Low Side Supply)
- Extended Temperature Range: -40°C to +125°C
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q101, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

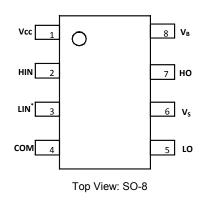
#### **Mechanical Data**

- Case: SO-8 (Type TH)
- Case Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminals: Finish—Matte Tin Plated Leads.
  Solderable per MIL-STD-202, Method 208 (£3)
- Weight: 0.075 grams (Approximate)





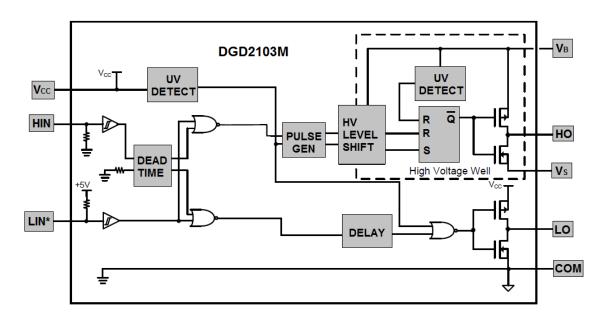
# Pin Diagrams



# **Pin Descriptions**

Pin Number	Pin Name	Function	
1	V <sub>CC</sub>	Logic and Low-Side Supply	
2	HIN	Logic Input for High-Side Gate Driver Output in Phase with HO	
3	LIN*	Logic Input for Low-Side Gate Driver Output out of Phase with LO	
4	COM	Low-Side and Logic Return	
5	LO	Low-Side Gate Drive Output	
6	Vs	High-Side Floating Supply Return	
7	НО	High-Side Gate Drive Output	
8	VB	High-Side Floating Supply	

# **Functional Block Diagram**





#### Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
High-Side Floating Supply Voltage	VB	-0.3 to +624	V
High-Side Floating Supply Offset Voltage	Vs	V <sub>B</sub> -24 to V <sub>B</sub> +0.3	V
High-Side Floating Output Voltage	V <sub>HO</sub>	V <sub>S</sub> -0.3 to V <sub>B</sub> +0.3	V
Offset Supply Voltage Transient	dVs / dt	50	V/ns
Low-Side Fixed Supply Voltage	V <sub>CC</sub>	-0.3 to +24	V
Low-Side Output Voltage	V <sub>LO</sub>	-0.3 to V <sub>CC</sub> +0.3	V
Logic Input Voltage (HIN and LIN*)	V <sub>IN</sub>	-0.3 to V <sub>CC</sub> +0.3	V

#### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor (Note 5)	PD	0.625	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	200	°C/W
Operating Temperature	TJ	+150	
Lead Temperature (Soldering, 10s)	TL	+300	°C
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	

Note: 5. When mounted on a standard JEDEC 2-layer FR-4 board.

## **Recommended Operating Conditions**

Parameter	Symbol	Min	Мах	Unit
High Side Floating Supply Absolute Voltage	VB	V <sub>S</sub> + 10	V <sub>S</sub> + 20	V
High Side Floating Supply Offset Voltage	Vs	(Note 6)	600	V
High Side Floating Output Voltage	V <sub>HO</sub>	Vs	VB	V
Low Side Supply Voltage	V <sub>CC</sub>	10	20	V
Low Side Output Voltage	VLO	0	Vcc	V
Logic Input Voltage (HIN & LIN*)	V <sub>IN</sub>	0	6	V
Ambient Temperature	TA	-40	+125	°C

Note: 6. Logic operation for  $V_S$  of -5V to +600V.



#### DC Electrical Characteristics (V<sub>BIAS</sub> (V<sub>CC</sub>, V<sub>BS</sub>) = 15V, @T<sub>A</sub> = +25°C, unless otherwise specified.) (Note 7)

Parameter	Symbol	Min	Тур	Max	Unit	Condition
Logic "1" (HIN) & Logic "0" (LIN*) Input Voltage	VIH	2.5	—		V	V <sub>CC</sub> = 10V to 20V
Logic "0" (HIN) & Logic "1" (LIN*) Input Voltage	V <sub>IL</sub>	_	—	0.8	V	V <sub>CC</sub> = 10V to 20V
High Level Output Voltage, V <sub>BIAS</sub> - V <sub>O</sub>	V <sub>OH</sub>	—	0.05	0.2	V	I <sub>O</sub> = 2mA
Low Level Output Voltage, V <sub>O</sub>	V <sub>OL</sub>	_	0.02	0.1	V	I <sub>O</sub> = 2mA
Offset Supply Leakage Current	I <sub>LK</sub>	—	_	50	μA	$V_{\rm B} = V_{\rm S} = 600 V$
Quiescent V <sub>BS</sub> Supply Current	I <sub>BSQ</sub>	—	60	100	μA	$V_{IN} = 0V \text{ or } 5V$
Quiescent V <sub>CC</sub> Supply Current	lccq	—	350	500	μA	$V_{IN} = 0V \text{ or } 5V$
Logic "1" Input Bias Current	I <sub>IN+</sub>	—	3	10	μA	HIN = 5V, LIN* = 0V
Logic "0" Input Bias Current	I <sub>IN-</sub>	—	_	5	μA	HIN = 0V, LIN* = 5V
V <sub>CC</sub> Supply Undervoltage Positive Going Threshold	V <sub>CCUV+</sub>	8.0	8.9	9.8	V	—
V <sub>CC</sub> Supply Undervoltage Negative Going Threshold	V <sub>CCUV-</sub>	7.4	8.2	9.0	V	—
V <sub>BS</sub> Supply Undervoltage Positive Going Threshold	V <sub>BSUV+</sub>	4.5	5.5	6.5	V	—
V <sub>BS</sub> Supply Undervoltage Negative Going Threshold	V <sub>BSUV-</sub>	4.2	5.2	6.2	V	—
Output High Short Circuit Pulsed Current	I <sub>O+</sub>	130	290	_	mA	$V_{O}$ = 0V, PW $\leq$ 10 $\mu$ s
Output Low Short Circuit Pulsed Current	I <sub>O-</sub>	270	600	—	mA	$V_{O}$ = 15V, PW $\leqslant$ 10 $\mu s$

Notes: 7. The V<sub>IN</sub> and I<sub>IN</sub> parameters are applicable to the two logic pins: HIN and LIN\*. The V<sub>O</sub> and I<sub>O</sub> parameters are applicable to the respective output pins: HO and LO.

8. For optimal operation, it is recommended that the input pulses (HIN and LIN\*) should have a minimum amplitude of 2.5V with a minimum pulse width of 840ns.

# **AC Electrical Characteristics** (V<sub>BIAS</sub> (V<sub>CC</sub>, V<sub>BS</sub>) = 15V, C<sub>L</sub> = 1000pF, @T<sub>A</sub> = +25°C, unless otherwise specified.)

Parameter	Symbol	Min	Тур	Max	Unit	Condition
Turn-On Propagation Delay	t <sub>ON</sub>		680	820	ns	V <sub>S</sub> = 0V
Turn-Off Propagation Delay	t <sub>OFF</sub>		150	220	ns	V <sub>S</sub> = 600V
Delay Matching, HO & LO Turn-On / Turn-Off	t <sub>DM</sub>		-	60	ns	—
Turn-On Rise Time	t <sub>R</sub>	_	70	170	ns	V <sub>S</sub> = 0V
Turn-Off Fall Time	tF	_	35	90	ns	V <sub>S</sub> = 0V
Deadtime: t <sub>DT LO-HO</sub> & t <sub>DT HO-LO</sub>	t <sub>DT</sub>	300	420	650	ns	—



# **Timing Waveforms**

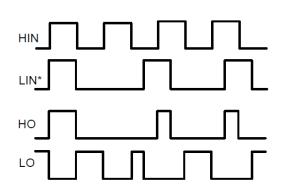
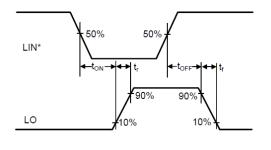


Figure 1. Input / Output Timing Diagram



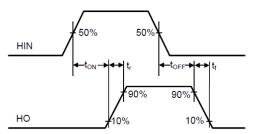


Figure 2. Switching Time Waveform Definitions

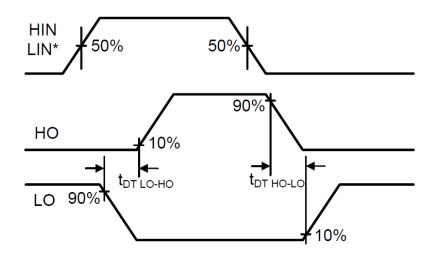


Figure 3. Deadtime Waveform Definitions



## Typical Performance Characteristics (Vcc=15V, @TA = +25°C, unless otherwise specified.)

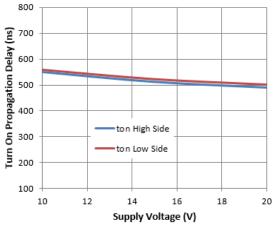


Figure 4. Turn-on Propagation Delay vs. Supply Voltage

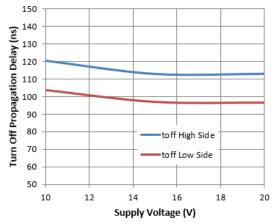
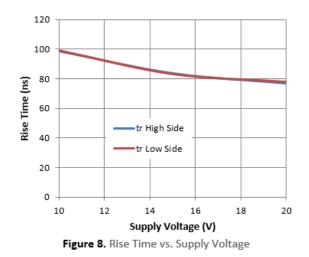


Figure 6. Turn-off Propagation Delay vs. Supply Voltage



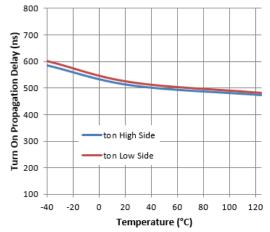


Figure 5. Turn-on Propagation Delay vs. Temperature

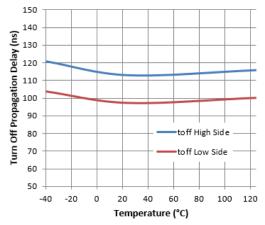
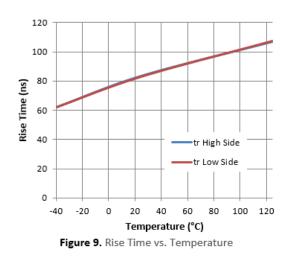


Figure 7. Turn-off Propagation Delay vs. Temperature





## Typical Performance Characteristics (continued)

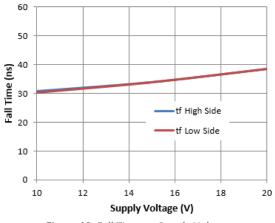


Figure 10. Fall Time vs. Supply Voltage

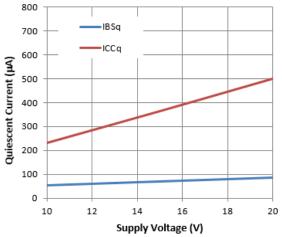
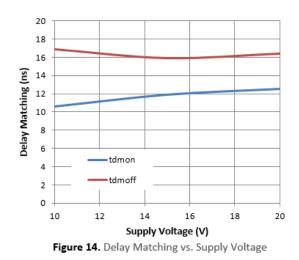


Figure 12. Quiescent Current vs. Supply Voltage



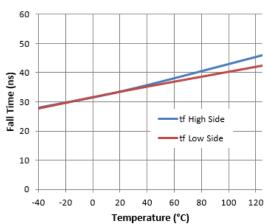
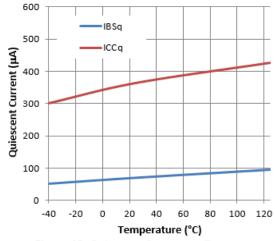


Figure 11. Fall Time vs. Temperature





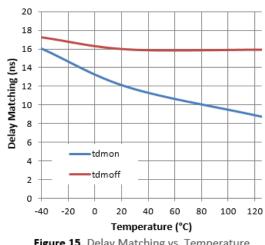


Figure 15. Delay Matching vs. Temperature



## Typical Performance Characteristics (cont.)

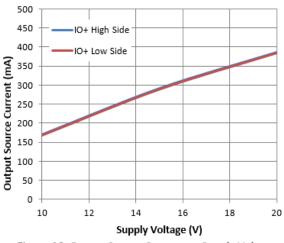


Figure 16. Output Source Current vs. Supply Voltage

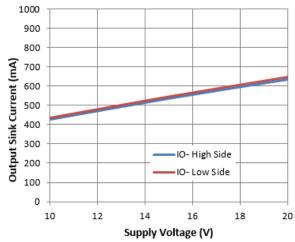


Figure 18. Output Sink Current vs. Supply Voltage

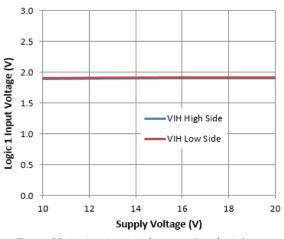


Figure 20. Logic 1 Input Voltage vs. Supply Voltage

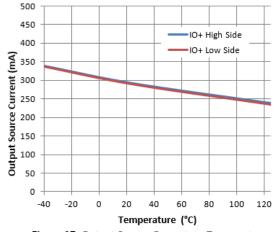
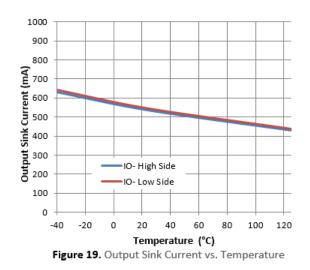
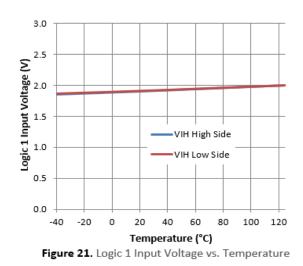


Figure 17. Output Source Current vs. Temperature







## Typical Performance Characteristics (cont.)

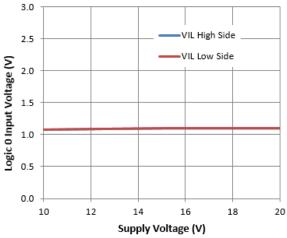


Figure 22. Logic 0 Input Voltage vs. Supply Voltage

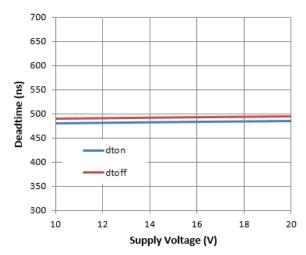
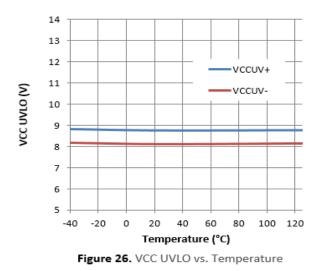


Figure 24. Deadtime vs. Supply Voltage



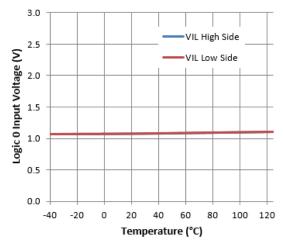


Figure 23. Logic 0 Input Voltage vs. Temperature

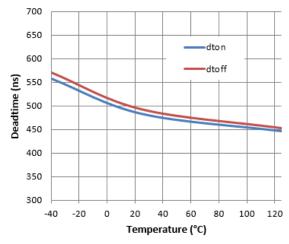


Figure 25. Deadtime vs. Temperature

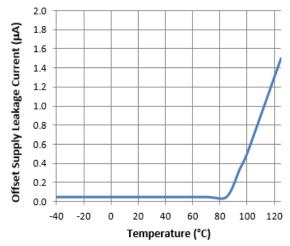
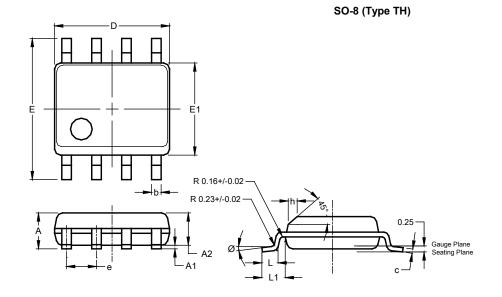


Figure 27. Offset Supply Leakage Current vs. Temperature



## **Package Outline Dimensions**

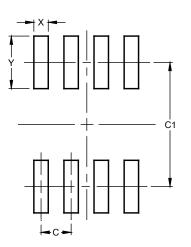
Please see http://www.diodes.com/package-outlines.html for the latest version.



SO-8 (Type TH)					
Dim	Min	Max	Тур		
Α	1.35	1.75			
A1	0.10	0.25			
A2			1.45		
b	0.35	0.51			
С	0.190	0.248			
D	4.80	5.00	4.90		
E	5.80	6.20	6.00		
E1	3.80	4.00	3.90		
е			1.27		
h	0.25	0.50			
L	0.41	1.27			
L1			1.04		
Ø	0°	8°			
All I	All Dimensions in mm				

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



SO-8 (Type TH)

Dimensions	Value (in mm)
С	1.27
C1	5.20
Х	0.60
Y	2.20

Note : For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



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